

Ultrasharp Crossover from Quantum to Classical Decay in a Quantum Dot Flanked by a Double-Barrier Tunneling Structure

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The decay of metastable states is dominated by quantum tunneling at low temperatures and by thermal activation at high temperatures. The escape rate of a particle out of a square well is calculated within a semi-classical approximation and exhibits an ‘ultrasharp’ crossover: a kink in the decay rate separates a *purely quantum* regime at low temperatures from a *purely thermal* regime at high temperatures. An experimental system – a quantum dot supplemented by a semiconductor heterostructure – that may be used to check the prediction, along with necessary experimental conditions, are described.

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The decay of metastable states[1] is a phenomenon of great generality, with realizations ranging from the creep of vortices in superconductors[2] to the decay of false vacua[3] in cosmology[4]. A particular interest of the decay phenomenon resides in the fact that it relates quantum to classical metastability: the decay rate is highly sensitive to temperature, it is dominated by quantum tunneling at low temperatures and by thermal activation at high temperatures.

A canonical example consists of a quantum mechanical particle in an asymmetric potential well, as illustrated in Fig. 1. Because of energetic metastability, sooner or later the particle leaves the well and escapes to the right. The decay rate Γ , defined as the inverse lifetime, depends on the form of the effective action at temperature T . At low T the particle occupies its ground state most of the time and escapes through quantum tunneling, so that $\Gamma \propto e^{-S(0)/\hbar}$, where $S(0)$ is the quantum mechanical action, while at high T the decay is Arrhenius-like, with $\Gamma \propto e^{-V_0/T}$.

Here, we calculate the decay rate of a particle initially residing in the well of Fig. 1, and find that the transition from quantum to classical behavior is ‘ultrasharp’: a singularity separates a purely quantum regime from a purely classical regime. From a theoretical point of view, this example is valuable as its semi-classical treatment is asymptotically exact for large V_0 . It also serves as a natural model to study an experimentally realizable mesoscopic object, namely a quantum dot supplemented by an adjacent double-barrier heterostructure. Below, we define the object in question more precisely and discuss the specific experimental conditions needed to observe an

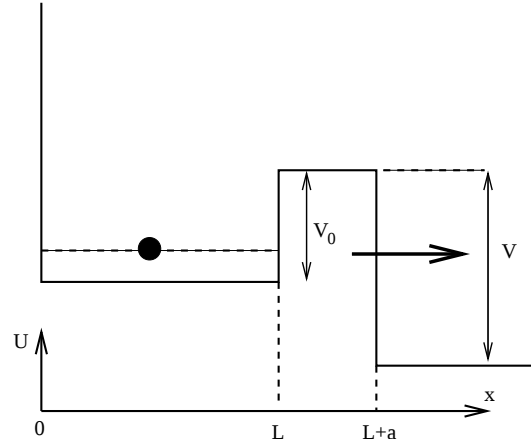


FIG. 1: Illustration of our simple theoretical model, consisting of a particle in a square well. Decay of the metastable state occurs by escape to the right (represented by the bold arrow).

ultrasharp crossover.

Before deriving specific results, we briefly describe general properties of the decay rate Γ . Mathematically, metastability may be encoded in imaginary corrections to the energy levels $E_n = \text{Re}E_n - i\hbar\Gamma_n/2$. Here $\text{Re}E_n$ are the energy levels in the large V_0 limit, in which the rates Γ_n are small (limit of ‘true metastability’). The probability $\mathcal{P} \propto |e^{-iE_nt/\hbar}|^2$ that the system occupies a given state then decays exponentially in time, according to $e^{-\Gamma_n t}$. If the lifetimes $1/\Gamma_n$ are larger than the local thermal equilibrium time, the initial preparation of the system is irrelevant; the particle fluctuates in low-energy states according to the Boltzmann distribution. Decay occurs because of rare fluctuations that drive the particle through the energy barrier. In field-theoretic language, these fluctuations correspond to imaginary time

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trajectories (instantons)[5] that come about as solutions to saddle-point equations and, as a result, impose an exponential dependence $\Gamma = A(T)e^{-S(T)/\hbar}$, where $S(T)$ is an effective action. For true metastability $S(T)/\hbar \gg 1$ and the main dependence of the decay rate upon temperature comes from the action as, typically, the temperature dependence of the prefactor $A(T)$ is weak.

Generically, the action $S(T)$ varies from the ground state action $S(0)$ at $T = 0$ to the high T Arrhenius limit $\hbar V_0/T$, where V_0 is the height of the energy barrier to overcome. This crossover, nevertheless, may occur in qualitatively different ways[6, 7, 8, 9, 10, 11, 12], depending on the shape of the trapping potential and the metastable dynamics[13], as illustrated on Fig. 2. For some metastable systems, the function $S(T)$ is smooth within the whole temperature range, but its second derivative is discontinuous at a critical temperature T_c (curve (a) on Fig. 2). Phase tunneling in a Josephson junction[14] constitutes a typical example of such a behavior. It may also happen that the derivative of S with respect to T has a discontinuity, resulting in a kink beyond which the behavior becomes purely classical (with $S \propto 1/T$) (curve (b) on Fig. 2). Such a singular temperature dependence was observed in Mn_{12} molecular magnets[15]. Our example yields yet another type of crossover, in which the quantum and classical behaviors are completely separated (curve (c) on Fig. 2): as before the decay rate is purely classical above the kink but, what is more, it is controlled by quantum tunneling *only* (with a *temperature-independent* action $S(0)$) below the kink. Such ultrasharp transitions are easier to detect experimentally, and might serve as useful tools for future investigations of macroscopic quantum phenomena.

We emphasize that the curves in Fig. 2 are qualitatively different. Curve (a) corresponds to the continuous deformation of a given instanton as the temperature is increased. By contrast, curve (b) results from the balance of two instantons, whose associated actions become equal at T_c . We note that below T_c , thermal fluctuations play a role as the effective action depends upon the temperature. Curve (c) is a limiting case of curve (b), in which the minimal action is the pure quantum action (corresponding to tunneling out of the ground state) up to T_c .

For the well of Fig. 1, the imaginary correction to the n th energy level E_n is proportional to $\exp(-S_{E_n}/\hbar)$, with S_{E_n} the usual semi-classical (WKB) action

$$S_{E_n} = 2\sqrt{2m(V_0 - E_n)}a. \quad (1)$$

If local thermal equilibrium is achieved fast enough, the particle in the well occupies states that are very close to stable ($V_0 \rightarrow \infty$) ones, with probabilities given by the Boltzmann weight. Thus, the decay rate reads

$$\Gamma \propto \sum_n \Gamma_n e^{-E_n/T}, \quad (2)$$

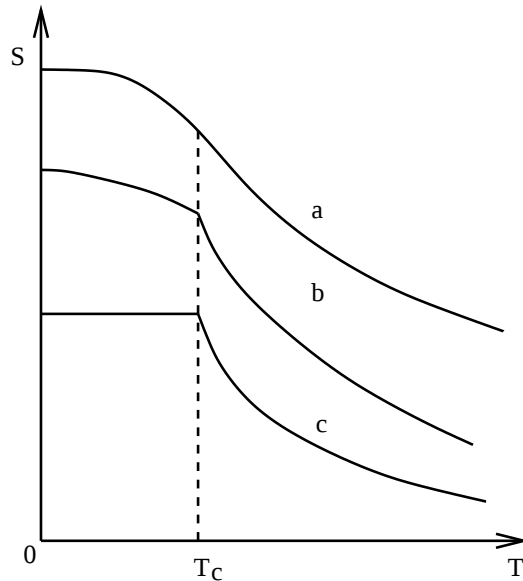


FIG. 2: Different types of crossover from quantum to classical decay: (a) smooth, (b) sharp, and (c) ultrasharp. At high T , thermal activation dominates and $S(T) \propto 1/T$ in all three curves.

with $\Gamma_n \propto e^{-S_{E_n}/\hbar} = e^{-2\sqrt{2m(V_0 - E_n)}a/\hbar}$. In the limit of true metastability, the sum in Eq. (2) runs over a large number of terms and is dominated by the largest contribution, to wit the one that minimizes the function

$$f(E) = \frac{S_E}{\hbar} + \frac{E}{T}. \quad (3)$$

It is easy to see that f has no local minimum in $[0, V_0]$ as its second derivative $\partial^2 f / \partial E^2$ is negative everywhere in the interval. Consequently, $f(E)$ takes its smallest value either at $E = 0$ (at low T) or at $E = V_0$ (at high T). Precisely,

$$\ln\left(\frac{1}{\Gamma}\right) \propto \frac{S(T)}{\hbar} = \begin{cases} \frac{2\sqrt{2mV_0}a}{\hbar}, & T < \frac{\hbar}{2a}\sqrt{\frac{V_0}{2m}} \equiv T_c, \\ \frac{V_0}{T}, & T > T_c. \end{cases} \quad (4)$$

Hence decay results either from purely quantum tunneling or from thermal activation out of the ground state. The ultrasharp crossover between the two is signaled by a kink in $S(T)$, as in curve (c) of Fig. 2.

We now discuss a possible experimental realization of the above model. In an experiment, information about decay rates can be extracted from the temperature dependence of the conductivity of a Coulomb blockaded quantum dot[16] flanked by a double-barrier heterostructure[17]. This setup is illustrated in Fig. 3. We assume that the left-hand barrier is much thinner than the right-hand one. In addition, we assume that strong decoherence hinders resonant tunneling and that electrons in the dot are properly equilibrated. Finally, our single-electron picture is valid if the energy of the

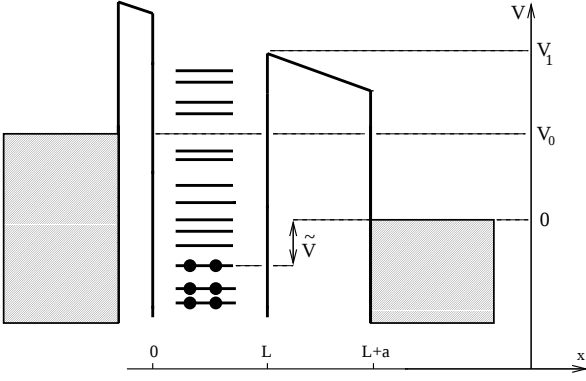


FIG. 3: Illustration of the experimental setup we propose in order to measure an ultrasharp crossover. An applied electric field imposes a bias to the right. With a left-hand barrier much thinner than the right-hand one and large electron-electron repulsion, current flows to the right *via* single-electron processes and the decay rate is determined only by tunneling and activation across the right-hand barrier.

electron-electron repulsion in the quasi-equilibrium, calculated *via* the addition of an electron to the quantum dot, is larger than $\tilde{V} + V_0$. Then the transport through the system is determined by tunneling to the right from the excited states with energies between 0 and V_0 . States with energies between V_0 and V_1 tunnel back quickly through the thin left-hand barrier and do not contribute to the current. Physically, charge transfer through this object occurs in two stages; first, rapid single-electron tunneling from the left-hand reservoir into the well and, second, electron escape into the right-hand reservoir after a relatively long dwelling time in the well.

The current I depends upon the temperature according to

$$I(T) \propto \exp\left(-\frac{\tilde{V}}{T}\right) \times \int_0^{V_0} dE \exp\left(-\frac{E}{T}\right) \exp\left(-\frac{2\sqrt{2m(V_1-E)}a}{\hbar}\right), \quad (5)$$

where we average the decay rates of single-electron states over the Boltzmann distribution and substitute the sum (analogous to that in Eq. (2)) by an integral, as the number of metastable levels in the well is large. Also, we assume that the temperature is small enough to neglect the smearing of the Fermi-Dirac distributions in the reservoirs. A saddle-point analysis similar to the one presented above yields a kink in the action at a critical temperature

$$T_{c, \text{dot}} = \frac{\hbar V_0}{2\sqrt{2ma}(\sqrt{V_1} - \sqrt{V_1 - V_0})}, \quad (6)$$

and, to exponential accuracy, the decay rate is given by

$\Gamma \propto \exp(-S_{\text{dot}}(T)/\hbar)$, with the effective action

$$\frac{S_{\text{dot}}(T)}{\hbar} = \begin{cases} \frac{\tilde{V}}{T} + \frac{2\sqrt{2mV_1}a}{\hbar}, & T < T_{c, \text{dot}}, \\ \frac{\tilde{V}+V_0}{T} + \frac{2\sqrt{2m(V_1-V_0)}a}{\hbar}, & T > T_{c, \text{dot}}. \end{cases} \quad (7)$$

This formula is valid for $V_1 > V_0$. For $V_1 < V_0$ one should substitute V_1 by V_0 . This leads to the disappearance of the quantum correction for $T > T_{c, \text{dot}}$. Due to the non-vanishing value of the energy gap $\tilde{V}$ between the Fermi levels of the dot and of the right-hand reservoir, an electron can tunnel only after having been raised in energy thermally, resulting in a classical contribution to the action below T_c . (This also explains why V_1 , rather than $V_1 + \tilde{V}$, appears for $T < T_{c, \text{dot}}$.) Experimentally, one monitors the singularity in $I(T)$ at $T = T_{c, \text{dot}}$, scanned by varying $\tilde{V}$ (through the gate voltage) and V_1 (through the Fermi energy of the left-hand reservoir). If $\tilde{V} \rightarrow 0$ and $V_1 \rightarrow V_0$, Eq. (7) reduces to the simpler dependence of Eq. (4).

If the electric field $\mathcal{E}$ that biases the system is too large, the potential is significantly distorted away from a square well. We thus require $a \ll L$. Otherwise, the action $S(T)$ is not given by Eq. (7) and one has to take a non-vanishing electric field into account. This, however, does not change the conclusion of the existence of a sharp crossover although it becomes less abrupt and may not be classified as ‘ultrasharp’ for large enough $\mathcal{E}$ [18]. Another experimental difficulty relates to the fact that real potentials are smeared compared to square wells; our theory is applicable if the characteristic size of the smearing is much smaller than the size a of the barrier. Within the quantum dot itself the potential is difficult to control; in order to observe an ultrasharp crossover one needs to flank the dot with a double-barrier structure. It is experimentally possible to create linear potentials using semiconductor heterostructures[17]—a potentially useful technique if the condition $a \ll L$ cannot be satisfied. The field $\mathcal{E}$ then can be chosen to yield a resulting rectangular right-hand barrier. The ultrasharp transition originates in the existence of a large enough region $L < x < L + a$ in which the potential does not vary substantially, while the detailed shape of the potential within the quantum dot itself is largely irrelevant.

Before concluding, we point out that the metastability condition $S(T) \gg \hbar$ cannot be satisfied in practice arbitrarily well. If the action $S(T)$ is too large, the tunneling time exceeds the duration of experiments, and no current is detected. Typically, one requires $S(T)/\hbar \lesssim 30$ in order to observe decay. Because of the finiteness of $S(T)$, the crossover from quantum to classical behavior is rounded over a narrow region, the width of which is estimated as follows. As long as the difference between classical and quantum actions, divided by $\hbar$, is of order 1, *i.e.*, as long

as

$$\left| \frac{S_0}{\hbar} - \frac{V_0}{T} \right| \lesssim 1, \quad (8)$$

neither of the two processes dominates over the other. Assuming $V_0/T_c \gg 1$ and expanding $1/T$ in $\Delta T = T - T_c$, we find that the crossover is rounded over an interval $\Delta T \simeq T_c^2/V_0 \ll T_c$.

In summary, we showed that the decay rate of a metastable electron in a rectangular well exhibits an ultrasharp transition from quantum to classical behavior: to exponential accuracy, decay results from quantum tunneling only, below a critical temperature T_c set by the barrier height, while above T_c , only thermal activation is relevant. Moreover, we described a semiconductor heterostructure that may be used to check our theoretical prediction, as well as some of the associated experimental restrictions.

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